

isc Silicon NPN Power Transistor

2SD1494

DESCRIPTION

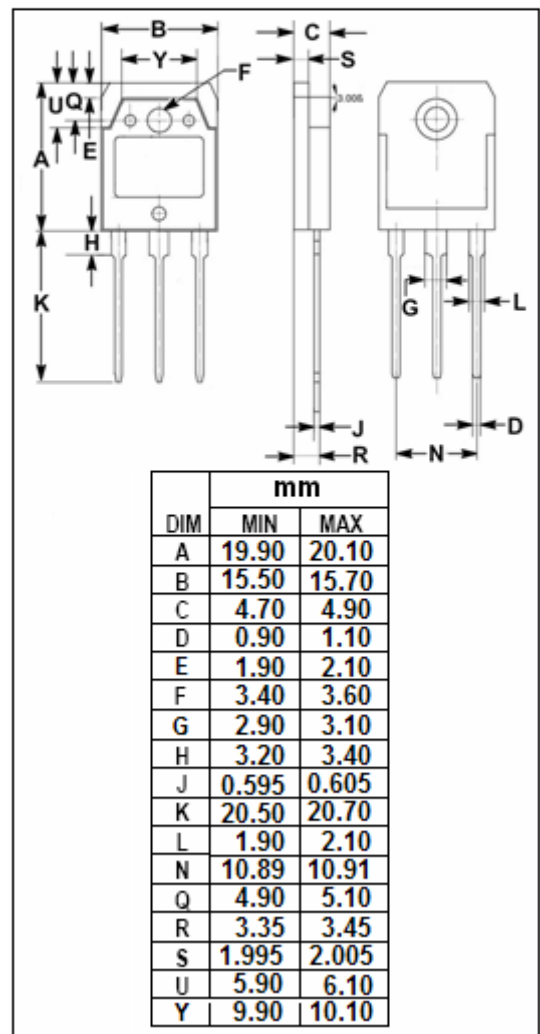
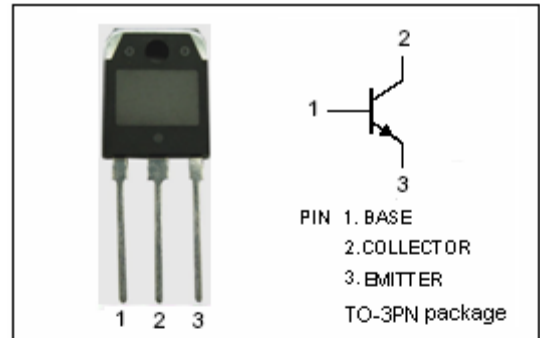
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V$  (Min)
- High Switching Speed

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	3	A
$I_{CM}$	Collector Current-Peak	6	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ C$	50	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-45~150	$^\circ C$



**isc Silicon NPN Power Transistor****2SD1494****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; R_{BE}=\infty$	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=600\text{V}; I_E=0$			10	$\mu\text{A}$
$t_f$	Fall Time	$I_C=2.75\text{A}, I_{B1}=0.6\text{A}, I_{B2}=-1.3\text{A}$			1.0	$\mu\text{s}$